Number	08:39 10:10 19:01 18:56
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[angl\$3 with dopant) [angl\$3 with dopant) [field adj effect adj transistor) and (ion adj implant) [angl\$3 with dopant) [angl\$3 w	10:10 19:01 18:56 13:44
- 2124 (field adj effect adj transistor) and (ion adj implant) - 6 438/525.ccls. and (field adj effect adj USPAT; USPGPUB; EPO; JPO; DERWENT USPAT; USPGPUB; EPO; JPO; DERWENT USPAT; U	10:10 19:01 18:56 13:44
- 2124 (field adj effect adj transistor) and (ion adj implant) - 6 438/525.ccls. and (field adj effect adj transistor) and (ion angl\$3 with dopant) - 85 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) - 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) - 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) - 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) - 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) - 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) - 5 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (lithography) - 0 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (jate adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (source	10:10 19:01 18:56 13:44
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- 85 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) - 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) - 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (gate adj electrode) and (source) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (gate adj electrode) and (source) and (gate adj implant) and (angl\$3 with dopant) and (gate adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (sour	18:56 13:44
adj implant) and (angl\$3 with dopant) (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (spare adj electrode) (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (gate adj electrode) and (drain) (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (gate adj electrode) and (source) and (drain) and (lithography) (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (gate adj electrode) and (source) and (gate adj electrode) and (source) and (drain) and (pocket adj region) 4 438/197.ccls. and (field adj effect adj transistor) and (ion adj implant) and (ion adj implant) and (US-PGPUB; EPO; JPO; DERWENT USPAT;	18:56 13:44
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- 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (USPAT; US-PGPUB; EPO; JPO; DERWENT adj implant) and (angl\$3 with dopant) and (USPAT; US-PGPUB; EPO; JPO; DERWENT adj implant) and (source) and (drain) - 5 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (gate adj electrode) and (source) and (drain) and (lithography) - 0 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; (gate adj electrode) and (source) and (source) and (gate adj electrode) and (source) and (source) and (drain) and (pocket adj region) - 4 438/197.ccls. and (field adj effect adj transistor) and (ion adj implant) and US-PGPUB;	13:44
- 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (JSPAT; (gate adj electrode) - 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (JSPAT; (gate adj electrode) and (source) and (gate adj electrode) and (source) and (gate adj electrode) and (source) and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (JSPAT; (gate adj electrode) and (source) and (source) and (gate adj electrode) and (source) an	13:44
adj implant) and (angl\$3 with dopant) and (JS-PGPUB; (gate adj electrode) 4 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (JS-PGPUB; (gate adj electrode) and (source) and (ion adj implant) and (angl\$3 with dopant) and (JS-PGPUB; (gate adj electrode) and (source) and (ion adj implant) and (angl\$3 with dopant) and (JS-PGPUB; (gate adj electrode) and (source) and (gate adj electrode) and (source) and (ion adj implant) and (angl\$3 with dopant) and (JS-PGPUB; (gate adj effect adj transistor) and (ion adj implant) and (pocket adj region) 4 438/197.ccls. and (field adj effect adj transistor) and (ion adj implant) and (JS-PGPUB; (JS-PGPUB; LS-PGPUB; LS-PG	13:44
(gate adj electrode) (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (uspat; (gate adj electrode) and (source) and (drain) (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (uspat; (gate adj electrode) and (source) and (drain) and (lithography) (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (uspat; (gate adj electrode) and (source) and (ion adj implant) and (angl\$3 with dopant) and (uspat; (gate adj electrode) and (source) and (uspat; (u	
- 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (uspAT; (gate adj electrode) and (source) and (ion adj implant) and (angl\$3 with dopant) and (ion adj implant) and (angl\$3 with dopant) and (uspAT; (gate adj electrode) and (source) and (drain) and (lithography) - 0 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (uspAT; (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (uspAT; (gate adj electrode) and (source) and (uspAT; (gate adj electrode) and (source) and (uspAT; (field adj effect adj uspAT; (aransistor) and (field adj effect adj uspAT; (aransistor) and (ion adj implant) and (uspAT; (uspAT; uspAT; u	
- 34 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (USPAT; (gate adj electrode) and (source) and (ion adj implant) and (angl\$3 with dopant) and (USPAT; (gate adj electrode) and (source) and (ion adj implant) and (lithography) - 0 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (USPAT; (gate adj electrode) and (source) and (ion adj implant) and (angl\$3 with dopant) and (USPAT; (gate adj electrode) and (source) and (uspate adj electrode) and (source) and (gate adj electrode) and (source) and (uspate adj electrode) and (uspate ad	
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(gate adj electrode) and (source) and (drain) and (lithography) (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (uspate adj electrode) and (source) and (gate adj electrode) and (source) and (drain) and (pocket adj region) 4 38/197.ccls. and (field adj effect adj transistor) and (ion adj implant) and (uspate adj uspate) 2003/06/20 2003/06/20	
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- 0 (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (USPAT; uS-PGPUB; (gate adj electrode) and (source) and (drain) and (pocket adj region) 4 38/197.ccls. and (field adj effect adj transistor) and (ion adj implant) and US-PGPUB;	
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(drain) and (pocket adj region) 4 438/197.ccls. and (field adj effect adj uspat; transistor) and (ion adj implant) and us-pgpub;	
4 438/197.ccls. and (field adj effect adj USPAT; 2003/06/20 transistor) and (ion adj implant) and US-PGPUB;	
transistor) and (ion adj implant) and US-PGPUB;	19.02
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(angl\$3 with dopant) DERWENT	
- 27 (field adj effect adj transistor) and (ion USPAT; 2003/06/20	19:04
adj implant) and (angl\$3 with dopant) and US-PGPUB;	
(gate adj electrode) and (source) and EPO; JPO;	
(drain) and (mask) DERWENT	
- 0 (field adj effect adj transistor) and (ion USPAT; 2003/06/20	19:05
adj implant) and (angl\$3 with dopant) and US-PGPUB;	
(gate adj electrode) and (source) and EPO; JPO;	
(drain) and (mask) and (conductive adj DERWENT	
region) - (field adj effect adj transistor) and (ion USPAT; 2003/06/20	10.05
	19.00
adj implant) and (angl\$3 with dopant) and US-PGPUB; (gate adj electrode) and (source) and EPO; JPO;	
(drain) and (mask) and (conductive adj DERWENT	
layer)	
6 (field adj effect adj transistor) and (ion USPAT; 2003/06/20	19:06
adj implant) and (angl\$3 with dopant) and US-PGPUB;	
(gate adj electrode) and (source) and EPO; JPO;	
(drain) and (mask) and (conduct\$3 adj DERWENT	
layer)	15 55
- 18 (field adj effect adj transistor) and (ion USPAT; 2003/06/21	15:51
adj implant) and (angl\$3 with dopant) and US-PGPUB;	
(gate adj electrode) and (source) and EPO; JPO;	
(drain) and (mask with electrode) DERWENT	16:05
- 12 (field adj effect adj transistor) and (ion USPAT; 2003/06/21 adj implant) and (angl\$3 with dopant) and US-PGPUB;	10.00
(gate adj electrode) and (source) and (EPO; JPO;	
(drain) and (mask with spacer) DERWENT	
1 (field adj effect adj transistor) and (ion USPAT; 2003/06/21	15.57
adj implant) and (angl\$3 with dopant) and US-PGPUB;	13:37
(gate adj electrode) and (source) and EPO; JPO;	13:37
(drain) and (mask with dielectric adj DERWENT	13:57
spacer)	13:37

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-	0	(field adj effect adj transistor) and (ion	USPAT;	2003/06/21 16:07
		adj implant) and (angl\$3 with dopant) and	US-PGPUB;	
		(gate adj electrode) and (source) and	EPO; JPO;	
	0	(drain) and (taper with electrode) (field adj effect adj transistor) and (ion	DERWENT USPAT;	2003/06/21 16:11
-	•	adj implant) and (angl\$3 with dopant) and	US-PGPUB;	2003/00/21 10.11
	,	(gate adj electrode) and (source) and	EPO; JPO;	
		(drain) and (taper\$2 with electrode)	DERWENT	
-	5	(field adj effect adj transistor) and (ion	USPAT;	2003/06/21 16:12
		adj implant) and (angl\$3 with dopant) and	US-PGPUB;	-
		(gate adj electrode) and (source) and	EPO; JPO;	
		(drain) and (reduced with electrode)	DERWENT	2002/06/27 08:41
-	0	EP-1263027\$.did.	USPAT; US-PGPUB;	2003/06/27 08:41
			EPO; JPO;	
			DERWENT	
_	2	EP-1263027-\$.did.	USPAT;	2003/06/27 09:04
			US-PGPUB;	
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			US-PGPUB;	
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-	4	512063.pn.	USPAT;	2003/06/27 08:58
			US-PGPUB; EPO; JPO;	
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_	2	5120637.pn.	USPAT;	2003/06/27 08:58
	_	31200311p	US-PGPUB;	
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-	2	5120673.pn.	USPAT;	2003/06/27 09:10
			US-PGPUB; EPO; JPO;	
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1_	0	JP-88317951-\$.did.	USPAT;	2003/06/27 09:23
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			EPO; JPO;	
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-	0	JP-2162738-\$.did.	USPAT;	2003/06/27 09:06
			US-PGPUB; EPO; JPO;	
			DERWENT	
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_	2	6501133.pn.	USPAT;	2003/06/27 09:15
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-	0	2020050621.pn.	USPAT;	2003/06/27 09:25
1			US-PGPUB; EPO; JPO;	
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_	0	2000648044.pn.	USPAT;	2003/06/27 09:17
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-	2	20020050621.pn.	USPAT;	2003/06/27 09:18
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-	1	JP-56048174-\$.did.	USPAT;	2003/06/27 09:23
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